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such a scanning exposure apparatus, and a method for producing an optical element which employs such a scanning exposure apparatus. B. Description of the Related Art As is well known, in a semiconductor integrated circuit, such as VLSI, etc., minute and complicated circuit patterns are usually formed over a wafer, etc., as a material to be processed, using photolithography. In the recent years, as the dimension of the circuit patterns is becoming finer, various exposure apparatuses have been invented to meet such a requirement. Among them, the scanning exposure apparatus is known as one suitable for obtaining a fine pattern with good dimensional accuracy. The scanning exposure apparatus is being used to form fine resist patterns, etc., in manufacturing processes for semiconductor integrated circuits. In the manufacturing processes of semiconductor integrated circuits, it is essential to keep the wafer surface as flat as possible to improve the light intensity, the light-focusing performance and the resolution. To be more specific, the wafer surface is kept in a plane as flat as possible by reducing the amount of warp of the wafer. On the other hand, in the scanning exposure apparatus, if the amount of warp of the wafer is large, the wafer deforms, so that the wafer position in the optical system including the projection optical system, etc., does not coincide with its predetermined position, resulting in exposure accuracy degradation. For this reason, in the scanning exposure apparatus, even if the wafer surface is kept as flat as possible, exposure accuracy degradation is inevitable, depending on the amount of warp of the wafer. To eliminate the exposure accuracy degradation due to the warp of